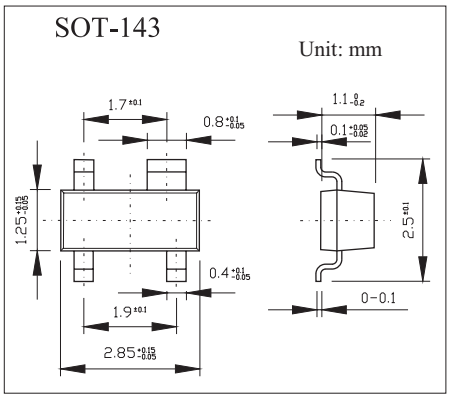
BAV23



■ Features

- Small plastic SMD package
- Switching speed: max. 50 ns
- General application
- Continuous reverse voltage:max. 200 V
- Repetitive peak reverse voltage:max. 250 V
- Repetitive peak forward current:max. 625 mA.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Test Condition	Min	Max	Unit
repetitive peak reverse voltage	V_{RRM}			250	V
repetitive peak reverse voltage	V_{RRM}	series connection		500	V
continuous reverse voltage	V_R			200	V
continuous reverse voltage	V_R	series connection		400	V
continuous forward current	I_F	single diode loaded		225	mA
		double diode loaded		125	mA
repetitive peak forward current	I_{FRM}	single diode loaded		625	mA
non-repetitive peak forward current	I_{FSM}	square wave; T_j = 25℃prior to surge			A
		t = 1 μs		9	
		t = 100 μs		3	
		t = 10 ms		1.7	
total power dissipation	P_{tot}	Tamb = 25℃		250	mW
storage temperature	T_{stg}		-65	+150	℃
junction temperature	T_j			150	℃
thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$			360	K/W
thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$			500	K/W

BAV23

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Condition	Min	Max	Unit
forward voltage	V_F	I_F = 100 mA		1.0	V
		I_F = 200 mA		1.25	V
reverse current	I_R	series connection			
		I_F = 100 mA		2.0	V
		I_F = 200 mA		2.5	V
forward voltage	V_F	V_R = 200 V		100	nA
		V_R = 200 V; T_j = 150℃		100	μA
reverse current	I_R	series connection			
		V_R = 60 V		100	nA
		V_R = 60 V;T_j = 150℃		100	μA
diode capacitance	C_d	f = 1 MHz; V_R = 0		5	pF
		series connection; f = 1 MHz;V_R = 0		2.5	pF
reverse recovery time	t_{rr}	when switched from I_F = 30 mA to,I_R = 30 mA; R_L = 100 Ω ; measured at I_R = 30 mA		50	ns

■ Marking

Marking	L30